B.Tech/AEIE/CSE/ECE/IT/2nd Sem/ECEN-1001/2016

2016

BASIC ELECTRONICS ENGINEERING (ECEN 1001)

Time Alloted : 3 Hours

Full Marks : 70

Figures out of the right margin indicate full marks. Candidates are required to answer Group A and <u>any 5 (five)</u> from Group B to E, taking <u>at least one</u> from each group. Candidates are required to give answer in their own words as far as practicable

<u>GROUP - A</u> (Multiple Choice Type Questions)

- 1. Choose the correct alternatives for the following : [10×1=10]
 - i) If the temperature of an n-type semiconductor is very high then it becomes
 - (a) more n-type (b) p-type
 - (c) intrinsic (d) none of these
 - ii) In Enhancement n-channel MOSFET, an induced n type channel can be produced between the source and the drain if
 - (a) $V_{GS} = 0$ (b) V_{GS} is positive

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(c) V_{GS} is negative (d) none of these

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iii) In a center tap full wave rectifier, if V_m is the peak voltage between center tap and one end of the secondary, the maximum voltage coming across the reverse bias diode is

(a) $V_{\rm m}$ (b) $2V_{\rm m}$ (c) $V_{\rm m}/2$ (d) $V_{\rm m}/\sqrt{2}$

- iv) The op amp can amplify
 - (a) AC signals only
 - (b) DC signals only
 - (c) both AC and DC signals
 - (d) neither AC not DC signals
- v) Avalanche breakdown is primarily dependent on the phenomenon of
 - (a) collision. (b) doping.
 - (c) ionization. (d) recombination.
- vi) The depletion region in an open circuited P-N junction contains
 - (a) electrons.
 - (b) holes.
 - (c) uncovered immobile impurity ions.
 - (d) neutralized impurity atoms.
- vii) In active region operation of a transistor
 - (a) both junctions are reversed biased.
 - (b) both junctions are forward biased.
 - (c) emitter junction is forward biased while collector junction is reverse biased.
 - (d) emitter junction is reversed biased while collector junction is forward biased.

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- viii) The best method of bias is
 - (a) base resistor method
 - (b) collector to base bias
 - (c) base bias with collector and emitter feedbacks
 - (d) voltage divider bias
- ix) When a reverse bias is applied to the gate of JFET, the depletion region width
 - (a) is uniform in the channel
 - (b) is wider near the source and tapers near drain
 - (c) is wider near drain and tapers near source
 - (d) is nil
- x) Positive feedback is used in
 - (a) amplifiers (b) rectifiers
 - (c) oscillators (d) detectors

GROUP - B

- 2. (a) Explain drift and diffusion of charge carrier in semiconductors.
 - (b) Distinguish between Zener breakdown and Avalanche breakdown.
 - (c) Explain how the Zener diode can be used for voltage regulation, with the help of proper circuit diagram.

4+5+3 = 12

3. (a) Explain the operation of a bridge rectifier with the help of a circuit diagram. Find the PIV.

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(b) Evaluate the ripple factor and efficiency of a half wave rectifier.

6+6 = 12

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GROUP - C

- 4. (a) What is transistor? Why is it so called? How it is biased?
 - (b) Explain the mechanism of current flow in a PNP transistors.
 - (c) A germanium transistor with a=0.98 gives a reverse saturation current $I_{CBO} = 10 \text{uA}$ in common base configuration. When transistor is used in CE configuration with a base current of 0.22 uA, calculate the collector current.

(1+1+1)+(5)+4 = 12

- 5. (a) Define Stability Factor of Bipolar Junction Transistor and state its significance.
 - (b) In a collector to base bias circuit indicated in Fig.1, a transistor with β = 100 is used. Supply voltage V_{CC} = 20V, V_{BE} = 0.7V, collector resistor R_C = 1k Ω . The bias is obtained by connecting 100K Ω resistor from collector to base. Find the Q-point and stability factor.



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4+8 = 12

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Group - D

- 6. (a) Describe the working principle of JFET with neat diagram.
 - (b) Explain how JFET can be used as a Voltage Variable Resistor (VVR).

6+6 = 12

- (a) Explain the basic construction of an enhancement type P-channel MOSFET. Draw and explain its static characteristics.
 - (b) In what respect, a JEFT differs from MOSFET?
 - (c) Define : The pinch-off voltage. (4+3)+3+2 = 12

GROUP - E

- 8. (a) What do you mean by feedback in amplifier? Define negative and positive feedbacks.
 - (b) Explain a feedback amplifier with the help of a block diagram.
 - (c) A negative feedback of β = 0.002 is applied to an amplifier of gain 1000.Calculate the change in overall gain of the feedback amplifier if the internal amplifier is subjected to a gain reduction of 15%.

(2+1+1)+4+4 = 12

- 9. (a) Draw and explain the circuit of (i) Voltage follower, (ii) Subtractor using op-amp.
 - (b) Describe the use of an op-amp as an integrator. Draw appropriate input and output waveforms.
 - (c) A 5 mV, 1 kHz sinusoidal signal is applied to the input of an op-amp integrator for which R = 100k Ω and C = 1 μ F.Calculate the output voltage.

4+4+4 = 12

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